

0.5W SILICON PLANAR ZENER DIODES

FEATURES

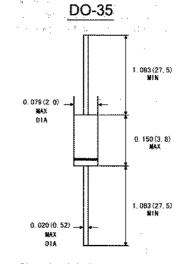
The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

. Case: DO-35 glass case

. Polarity: Color band denotes cathode end

. Weight: Approx. 0.13gram



Dimensions in Inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA= 25° C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at Ta=50°C	Ptot	5001)	mW
Junction temperature	TJ	175	$^{\circ}$
Storage temperature range	Тѕтс	-65 to + 175	${\mathbb C}$

ELECTRICAL CHARACTERISTICS(TA=25°C)

	Symbols Min. Typ.							
Thermal resistance junction to ambient	RθJA			3001)	K/W			
Forward voltage at IF=100mA	VF			1	V			
1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature								



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BXZ55... SILICON PLANAR ZENER DIODES

Туре	Zener Voltage Range ₁₎			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage
туре	Vznom	Izt for Vzt 2)		rzjt and rzjk at Izk			IR and IR 2) at VR			TKvz
	V	mA	V	Ω	Ω	mA	μА	μд	V	%/K
BZX 55/C 0V8 3)	0.8		0.730.83	<8	<50		-	1	-	-0.260.23
BZX 55/C 2V0	2.0		1.92.1				<100	<200		
BZX 55/C 2V4	2.4		2.282.56				<50	<100		-0.090.06
BZX 55/C 2V7	2.7		2.52.9				<10	<50		
BZX 55/C 3V0	3		2.83.2	<85			<4			
BZX 55/C 3V3	3.3		3.13.5		<600		<40		-0.080.05	
BZX 55/C 3V6	3.6		3.43.8			<2	<2		<1	-0.080.03
BZX 55/C 3V9	3.9		3.74.1							
BZX 55/C 4V3	4.3		4.04.6	<75			<1	<20		-0.060.03
BZX 55/C 4V7	4.7		4.45.0	<60			<0.5	<10		-0.05+0.02
BZX 55/C 5V1	5.1		4.85.4	<35	<550					-0.02+0.02
BZX 55/C 5V6	5.6		5.26.0	<25	<450					-0.05+0.05
BZX 55/C 6V2	6.2	5	5.86.6	<10	<200	1			2.0	0.030.06
BZX 55/C 6V8	6.8		6.47.2	<8	<150				3.0	0.030.07
BZX 55/C 7V5	7.5		7.07.9	<7					5.0	0.030.07
BZX 55/C 8V2	8.2		7.78.7	<7	<50				6.2	0.030.08
BZX 55/C 9V1	9.1		8.59.6	<10					6.8	0.030.09
BZX 55/C 10	10		9.410.6	<15	<70		<0.1	<2	7.5	0.030.1
BZX 55/C 11	11		10.411.6	<20	<70				8.2	
BZX 55/C 12	12		11.412.7	<20	<90				9.1	
BZX 55/C 13	13		12.414.1	<26	<110				10.0	
BZX 55/C 15	15		13.815.6	<30	<110				11.0	0.030.11
BZX 55/C 16	16		15.317.1	<40	<170				12	
BZX 55/C 18	18		16.819.1	<50	<170				13	
BZX 55/C 20	20		18.821.2	<55	<220				15	



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BZX 55/C 22	22		20.823.3	<55					16	
BZX 55/C 24	24	1	22.825.6	<80					18	
BZX 55/C 27	27	5	25.128.9]	1		<2	20	
BZX 55/C 30	30		2832		<220				22	
BZX 55/C 33	33		3135	<80					24	
BZX 55/C 36	36	1	3438						27	
BZX 55/C 39	39		3741		<500				30	
BZX 55/C 43	43	1	4046		<500			<5	33	0.040.12
BZX 55/C 47	47	1	4450		<600		<0.1		36	
BZX 55/C 51	51	1	4854		<700	0.5			39	
BZX 55/C 56	56	2.5	5260		<700				43	
BZX 55/C 62	62		5866		<1000				47	
BZX 55/C 68	68		6472						51	
BZX 55/C 75	75		7079						56	
BZX 55/C 82	82		7787		<1500				62	
BZX 55/C 91	91		8596		<2000				68	
BZX 55/C 100	100		94106		<5000			<10	75	
BZX 55/C 110	110	1	104116		<5000	0.1			82	0.050.12
BZX 55/C 120	120		114127		<5500				91	
BZX 55/C 130	130		124141		<6000				100	
BZX 55/C 150	150		138156		<6500				110	
BZX 55/C 160	160		153171		<7000				120	
BZX 55/C 180	180		168191		<8500				130	
BZX 55/C 200	200		188212		<10000				150	

¹⁾Tested with pulses tp=20ms

²⁾Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

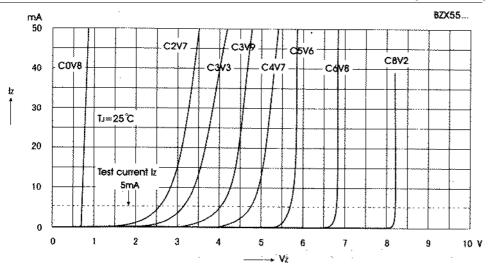
³⁾The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.



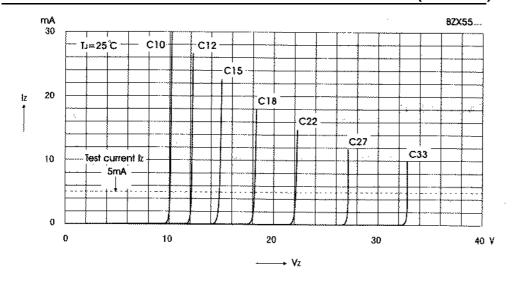
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BREAKDOWN CHARACTERISTICS AT TJ=CONSTANT(PULSED)



BREAKDOWN CHARACTERISTICS AT TJ=CONSTANT(PULSED)



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